



PN 3569

NPN SILICON PLANAR EPITAXIAL TRANSISTOR

MICRO ELECTRONICS

GENERAL DESCRIPTION :

The PN 3569 is an NPN silicon planar epitaxial transistor designed for amplifier and switching applications for collector current up to 500mA.

MECHANICAL OUTLINE

TO-92A



EBC

ABSOLUTE MAXIMUM RATINGS :

Continuous Power Dissipation @ $T_A=25^{\circ}\text{C}$ , $P_d$	0.3W
Continuous Power Dissipation @ $T_C=25^{\circ}\text{C}$ , $P_d$	0.8W
Maximum Collector Junction Temperature, $T_j$	$125^{\circ}\text{C}$
Storage Temperature Range, $T_{stg}$	$-55^{\circ}\text{C}$ to $+125^{\circ}\text{C}$
Soldering Temperature (10 sec. time limit)	$260^{\circ}\text{C}$
Collector to Base Voltage, $V_{CBO}$	80V
Collector to Emitter Voltage, $V_{CEO}$	40V
Emitter to Base Voltage, $V_{EBO}$	5V

ELECTRICAL CHARACTERISTICS @  $T_A=25^{\circ}\text{C}$  (unless otherwise stated) :

PARAMETER	SYMBOL	MIN	MAX	UNIT	TEST CONDITIONS
Collector-Base Breakdown Voltage	$BV_{CBO}$	80		V	$I_C=100\mu\text{A}$ $I_E=0$
Collector-Emitter Sustaining Voltage	$V_{CEO(sust)}^*$	40		V	$I_C=30\text{mA}$ $I_B=0$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	5		V	$I_E=10\mu\text{A}$ $I_C=0$
Collector Cutoff Current	$I_{CBO}$		50	nA	$V_{CB}=40\text{V}$ $I_E=0$
Collector Cutoff Current	$I_{CBO}$		5	$\mu\text{A}$	$V_{CB}=40\text{V}$ $I_E=0$ $T_A=75^{\circ}\text{C}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.25	V	$I_C=150\text{mA}$ $I_B=15\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.1	V	$I_C=150\text{mA}$ $I_B=15\text{mA}$
D.C. Current Gain	$h_{FE}^*$	100	300		$V_{CE}=1\text{V}$ $I_C=150\text{mA}$

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